

<b>SANYO</b>	No.3810	<b>2SJ225</b>
	P-Channel MOS Silicon FET	
Very High-Speed Switching Applications		

**Features**

- Small ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Meets radial taping.

**Absolute Maximum Ratings at Ta = 25°C**

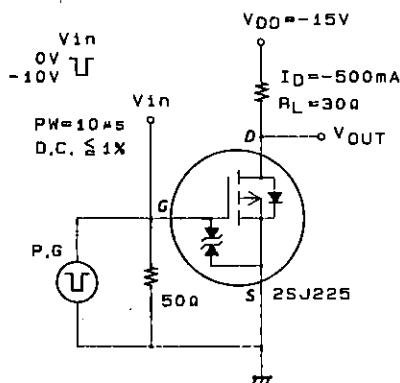
			unit
Drain to Source Voltage	V <sub>DSS</sub>	-30	V
Gate to Source Voltage	V <sub>GSS</sub>	±15	V
Drain Current (DC)	I <sub>D</sub>	-1	A
Drain Current (Pulse)	I <sub>DP</sub>	-4	A
Allowable Power Dissipation	P <sub>D</sub>	1	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

PW ≤ 10 μs, duty cycle ≤ 1%

**Electrical Characteristics at Ta = 25°C**

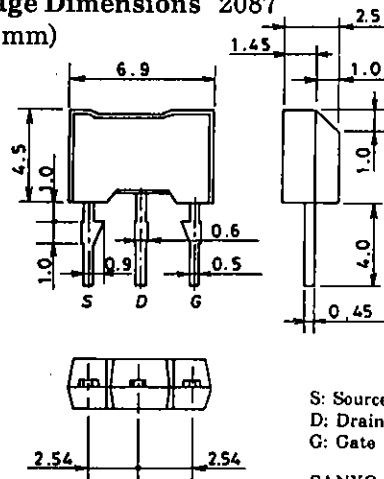
		min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-30		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0		-100	μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0		±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA	-1.0	-2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -500mA	0.6	1.0	S
Static Drain to Source on State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = -500mA, V <sub>GS</sub> = -10V	0.5	0.75	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		170	pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		110	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		20	pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		10	ns
Rise Time	t <sub>r</sub>	∕		13	ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	∕		70	ns
Fall Time	t <sub>f</sub>	∕		30	ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0.		-0.9	V

**Switching Time Test Circuit**



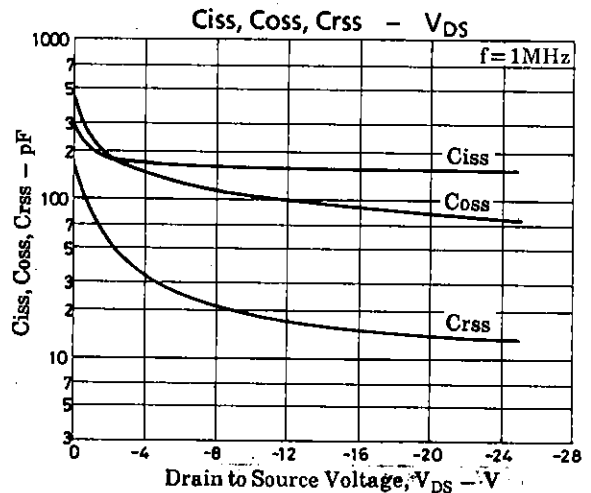
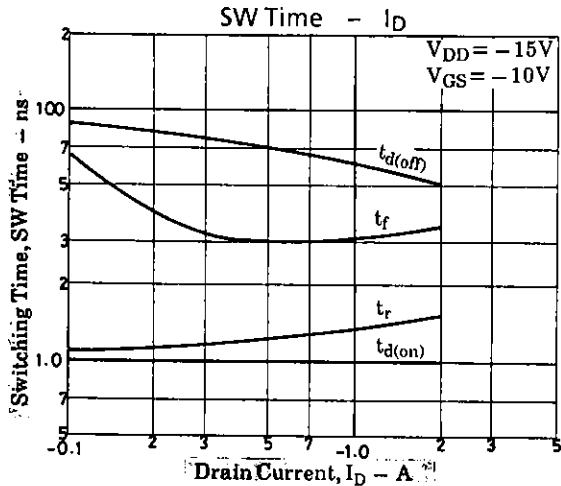
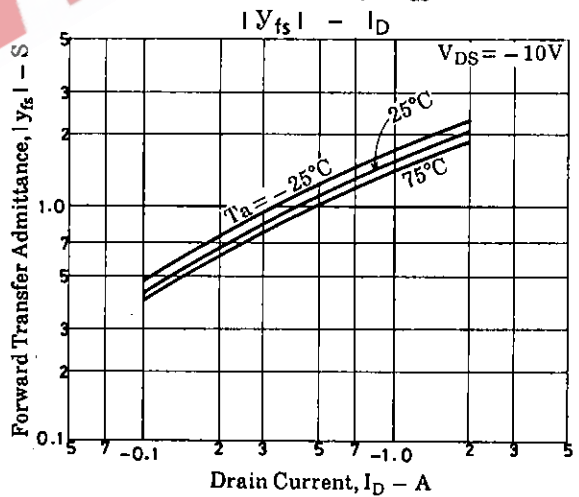
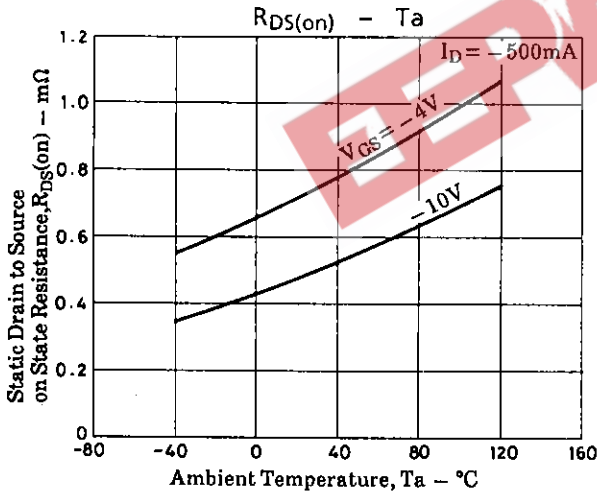
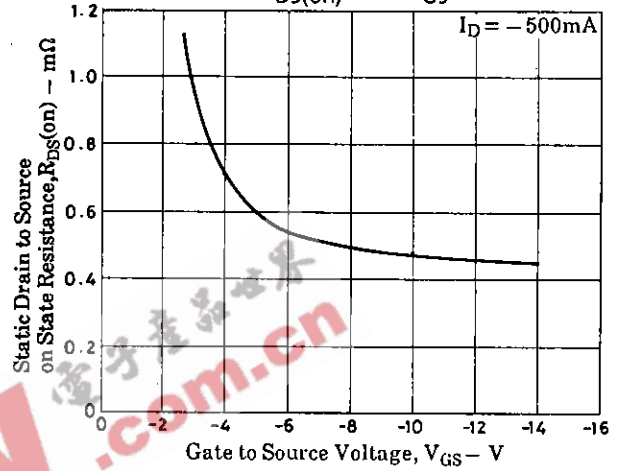
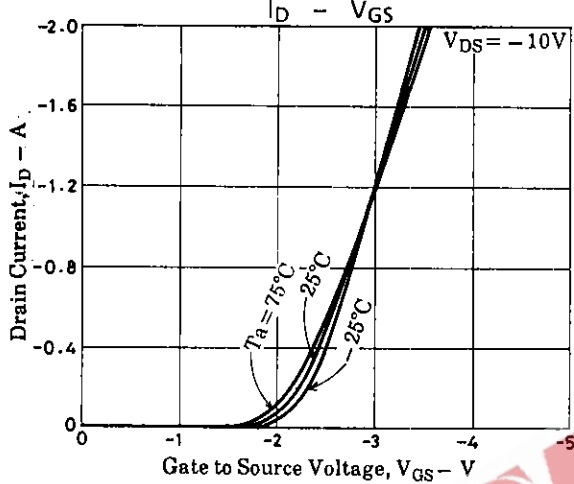
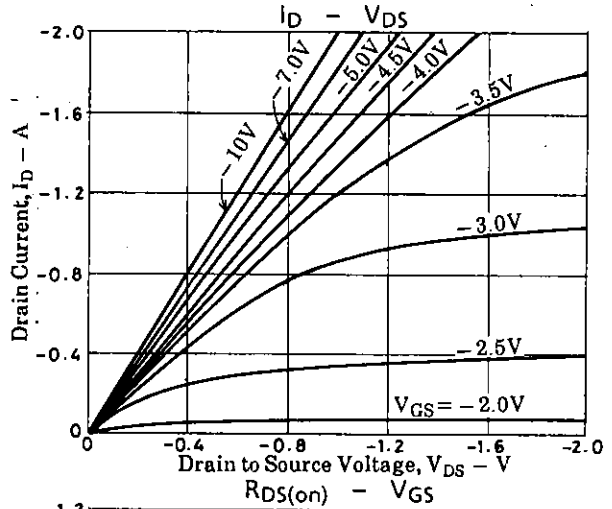
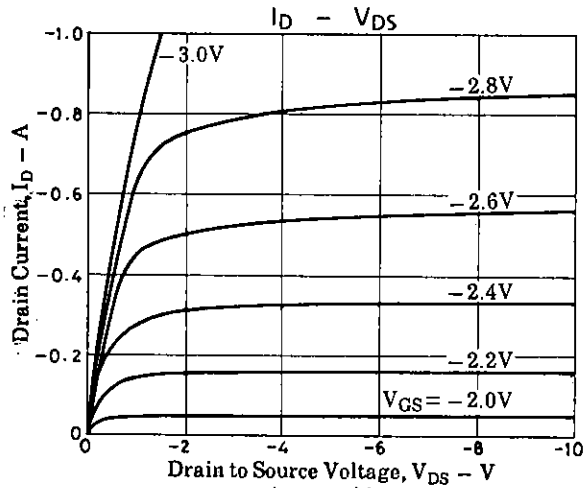
**Package Dimensions 2087**

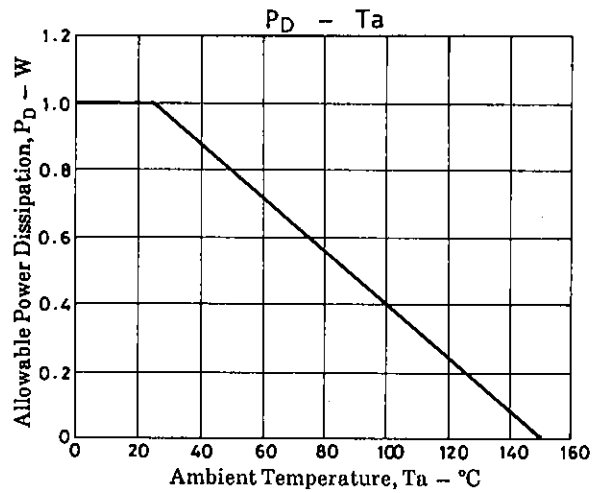
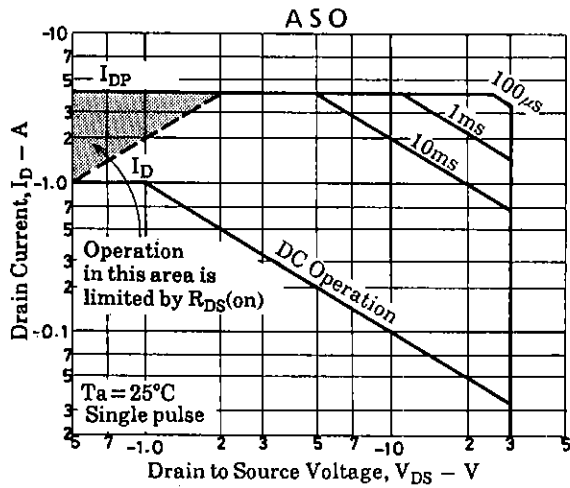
(unit : mm)



S: Source  
D: Drain  
G: Gate

SANYO: NMP





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